

# 제22회 한국반도체학술대회

2015년 2월 10일(화) - 12일(목), 인천 송도컨벤시아

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## E. Compound Semiconductors 분과

Room E  
1F / 108호

2015년 2월 11일(수) 09:00-10:30

### [WE1-E] Material Characteristic

좌장: 오정우 (연세대학교), 민병규 (한국전자통신연구원)

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| WE1-E-1 | 09:00-09:15 | <b>Extraction of Interface Trap Density by using Frequency Dispersion of C-V in Normally-off Gate-Recessed AlGaIn/GaN HFETs</b><br>Sungju Choi <sup>1</sup> , Youngjin Kang <sup>2</sup> , Jonghwa Kim <sup>1</sup> , Jungmok Kim <sup>1</sup> , Sung-Jin Choi <sup>1</sup> , Dong Myong Kim <sup>1</sup> , Ho-Young Cha <sup>2</sup> , Hyungtak Kim <sup>2</sup> , and Dae Hwan Kim <sup>1</sup><br><sup>1</sup> School of Electrical Engineering, Kookmin University, <sup>2</sup> School of Electronic and Electrical Engineering, Hongik University |
| WE1-E-2 | 09:15-09:30 | <b>Interfacial Reactions of Si/Ti/Al/Cu Ohmic Metallization on AlGaIn/GaN Heterostructures</b><br>Seonno Yoon, Jangwon Bang, and Jungwoo Oh<br>School of Integrated Technology, Yonsei University   |
| WE1-E-3 | 09:30-09:45 | <b>AlN/GaN 이종접합구조의 성장 및 소자제작을 통한 특성 확인</b><br>김정길, 원철호, 김동석, 강희성, 조우영, 김도균, 손동혁, 이준혁, 김지현, 이정희<br>경북대학교 IT 대학 전자공학부   |
| WE1-E-4 | 09:45-10:00 | <b>Correlation between 2-DEG Mobility and Crystal Quality in AlGaIn/GaN HEMT Structure Grown on 4H-SiC</b><br>Cheon Heo, Jongjin Jang, Kyungjae Lee, Byungchan So, Kyungbae Lee, and Okhyun Nam<br>Department of Nano-Optical Engineering, Korea Polytechnic University   |
| WE1-E-5 | 10:00-10:15 | <b>Fabrication of through-Hole n-Electrode for GaN Buffer Layer Removed UV Flip Chip LED</b><br>Anil Kawan, Jong Min Park, and Soon Jae Yu<br>Department of Electronic Engineering, Sunmoon University  |
| WE1-E-6 | 10:15-10:30 | <b>InGaAs-on Insulator Transistors with Y<sub>2</sub>O<sub>3</sub> Buried Oxide Layer</b><br>SangHyeon Kim, Dae-Myeong Geum, Min-Su Park, and Won Jun Choi<br>Center for Opto-electronic convergence systems, Korea Institute of Science and Technology   |